

## Advanced Power MOSFET

# SFH9244

### FEATURES

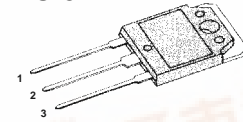
- ❑ Avalanche Rugged Technology
- ❑ Rugged Gate Oxide Technology
- ❑ Lower Input Capacitance
- ❑ Improved Gate Charge
- ❑ Extended Safe Operating Area
- ❑ Lower Leakage Current : 10  $\mu$ A (Max.) @  $V_{DS} = -250V$
- ❑ Lower  $R_{DS(ON)}$  : 0.549  $\Omega$  (Typ.)

$$BV_{DSS} = -250 V$$

$$R_{DS(on)} = 0.8 \Omega$$

$$I_D = -8.7 A$$

#### TO-3P



1. Gate 2. Drain 3. Source

### Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	-250	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ C$ )	-8.7	A
	Continuous Drain Current ( $T_C=100^\circ C$ )	-6.0	
$I_{DM}$	Drain Current-Pulsed ①	-35	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy ②	473	mJ
$I_{AR}$	Avalanche Current ①	-8.7	A
$E_{AR}$	Repetitive Avalanche Energy ①	12.6	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-4.8	V/ns
$P_D$	Total Power Dissipation ( $T_C=25^\circ C$ )	126	W
	Linear Derating Factor	1.0	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds	300	

### Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.0	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink	0.24	--	
$R_{\theta JA}$	Junction-to-Ambient	--	40	

### Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	-250	--	--	V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
ΔBV/ΔT <sub>J</sub>	Breakdown Voltage Temp. Coeff.	--	-0.22	--	V/°C	I <sub>D</sub> =-250μA <b>See Fig 7</b>
V <sub>GS(th)</sub>	Gate Threshold Voltage	-2.0	--	-4.0	V	V <sub>DS</sub> =-5V, I <sub>D</sub> =-250μA
I <sub>GSS</sub>	Gate-Source Leakage, Forward	--	--	-100	nA	V <sub>GS</sub> =-30V
	Gate-Source Leakage, Reverse	--	--	100		V <sub>GS</sub> =30V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	--	--	-10	μA	V <sub>DS</sub> =-250V
		--	--	-100		V <sub>DS</sub> =-200V, T <sub>C</sub> =125°C
R <sub>DS(on)</sub>	Static Drain-Source On-State Resistance	--	--	0.8	Ω	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.4A ④
g <sub>fs</sub>	Forward Transconductance	--	5.8	--	S	V <sub>DS</sub> =-40V, I <sub>D</sub> =-4.4A ④
C <sub>iss</sub>	Input Capacitance	--	1205	1565	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1MHz <b>See Fig 5</b>
C <sub>oss</sub>	Output Capacitance	--	175	265		
C <sub>rss</sub>	Reverse Transfer Capacitance	--	65	100		
t <sub>d(on)</sub>	Turn-On Delay Time	--	14	40	ns	V <sub>DD</sub> =-125V, I <sub>D</sub> =-8.6A, R <sub>G</sub> =9.1Ω <b>See Fig 13</b> ④ ⑤
t <sub>r</sub>	Rise Time	--	21	50		
t <sub>d(off)</sub>	Turn-Off Delay Time	--	47	105		
t <sub>f</sub>	Fall Time	--	18	45		
Q <sub>g</sub>	Total Gate Charge	--	45	58	nC	V <sub>DS</sub> =-200V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-8.6A <b>See Fig 6 &amp; Fig 12</b> ④ ⑤
Q <sub>gs</sub>	Gate-Source Charge	--	8.7	--		
Q <sub>gd</sub>	Gate-Drain("Miller") Charge	--	23.4	--		

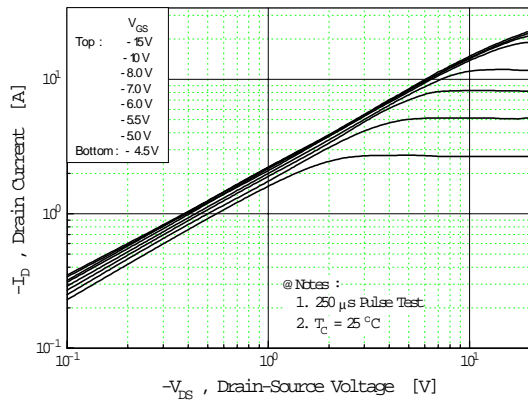
### Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I <sub>S</sub>	Continuous Source Current	--	--	-8.7	A	Integral reverse pn-diode in the MOSFET
I <sub>SM</sub>	Pulsed-Source Current ①	--	--	-35		
V <sub>SD</sub>	Diode Forward Voltage ④	--	--	-5.0	V	T <sub>J</sub> =25°C, I <sub>S</sub> =-8.7A, V <sub>GS</sub> =0V
t <sub>rr</sub>	Reverse Recovery Time	--	210	--	ns	T <sub>J</sub> =25°C, I <sub>F</sub> =-8.6A
Q <sub>rr</sub>	Reverse Recovery Charge	--	1.82	--	μC	di <sub>F</sub> /dt=100A/μs ④

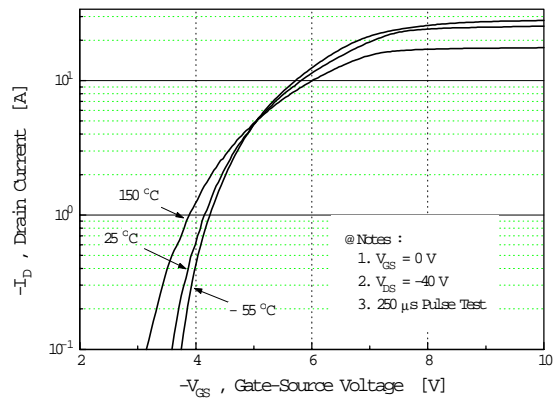
#### Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=10mH, I<sub>AS</sub>=-8.7A, V<sub>DD</sub>=-50V, R<sub>G</sub>=27Ω\*, Starting T<sub>J</sub>=25°C
- ③ I<sub>SD</sub> < -8.6A, di/dt < 450A/μs, V<sub>DD</sub> < BV<sub>DSS</sub>, Starting T<sub>J</sub>=25°C
- ④ Pulse Test : Pulse Width = 250μs, Duty Cycle < 2%
- ⑤ Essentially Independent of Operating Temperature

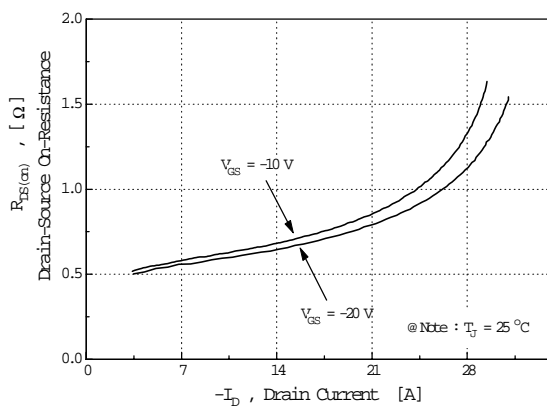
**Fig 1. Output Characteristics**



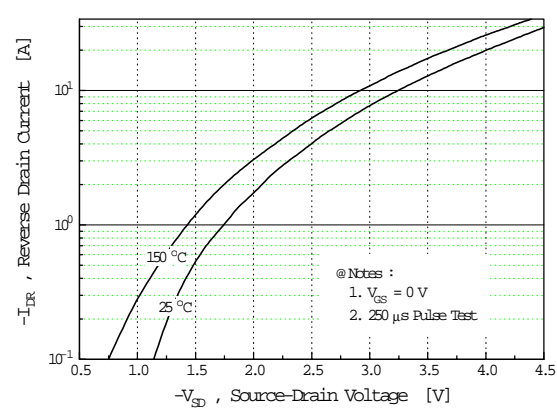
**Fig 2. Transfer Characteristics**



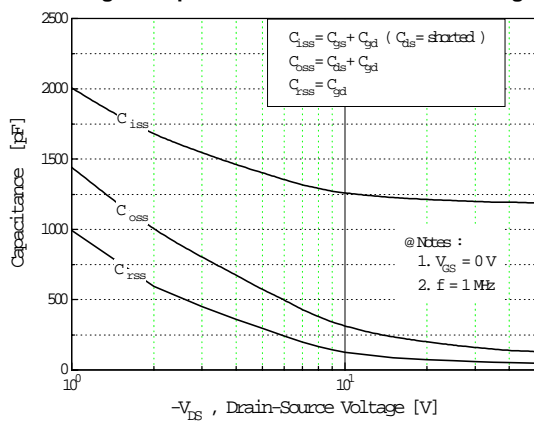
**Fig 3. On-Resistance vs. Drain Current**



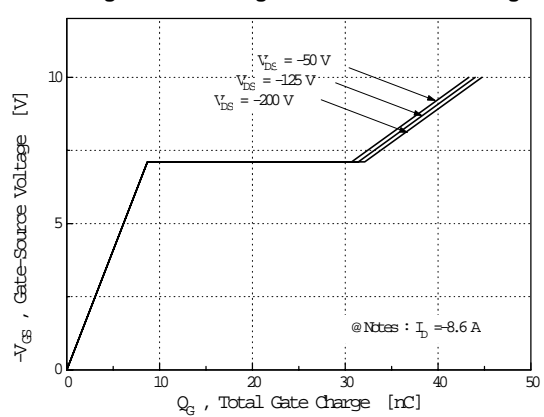
**Fig 4. Source-Drain Diode Forward Voltage**



**Fig 5. Capacitance vs. Drain-Source Voltage**



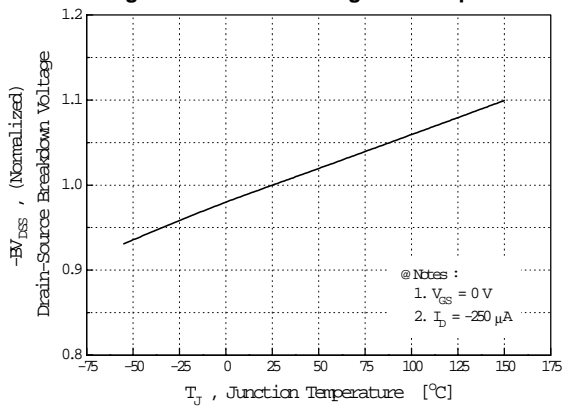
**Fig 6. Gate Charge vs. Gate-Source Voltage**



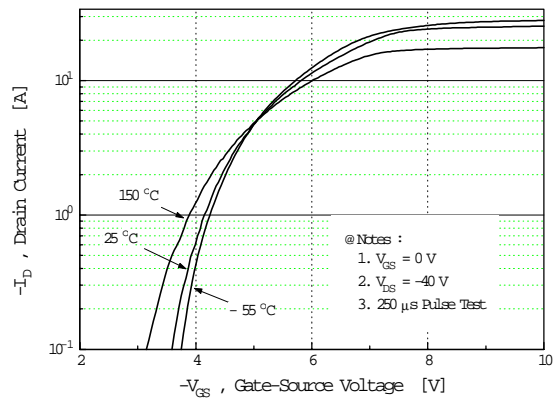
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# P-CHANNEL POWER MOSFET

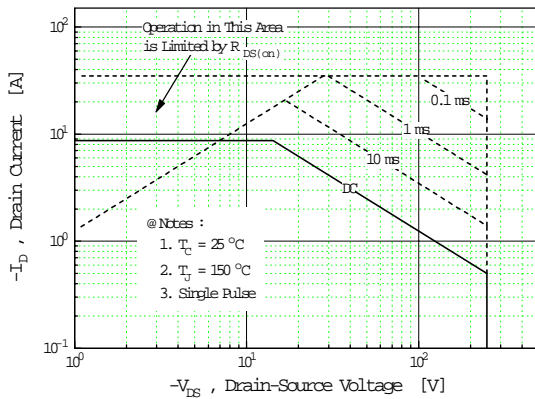
**Fig 7. Breakdown Voltage vs. Temperature**



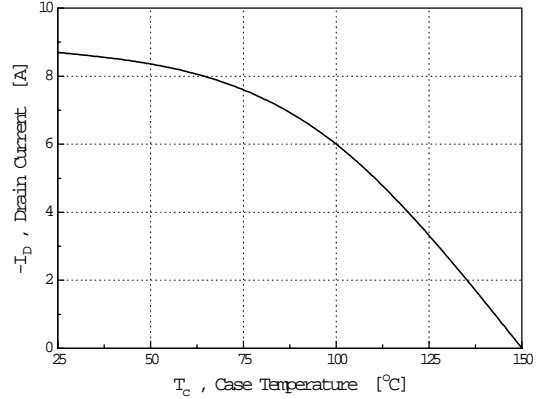
**Fig 8. On-Resistance vs. Temperature**



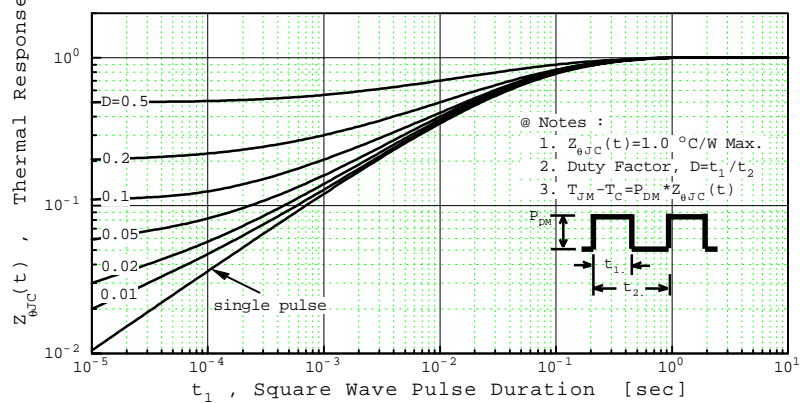
**Fig 9. Max. Safe Operating Area**



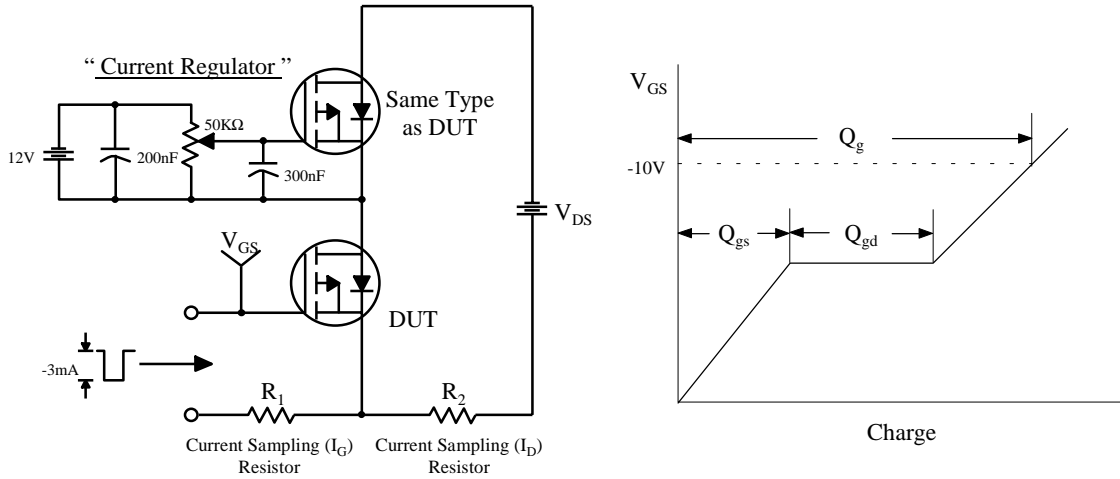
**Fig 10. Max. Drain Current vs. Case Temperature**



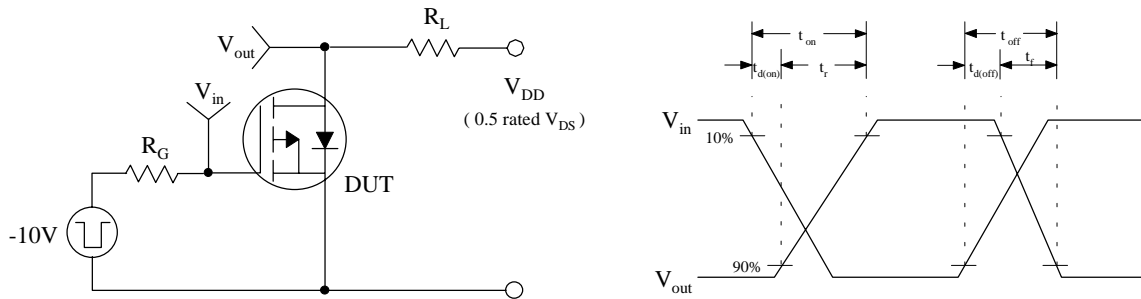
**Fig 11. Thermal Response**



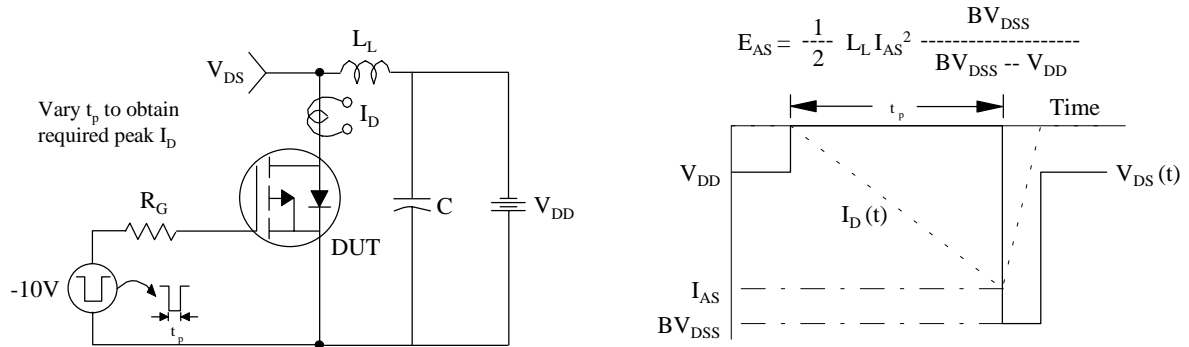
**Fig 12. Gate Charge Test Circuit & Waveform**



**Fig 13. Resistive Switching Test Circuit & Waveforms**



**Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms**





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